

NVMFS6B14N

Power MOSFET

100 V, 15 mΩ, 55 A, Single N-Channel

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS6B14NWF – Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	100	V
Gate-to-Source Voltage			V _{GS}	±16	V
Continuous Drain Current R _{θJC} (Notes 1, 2, 3)	Steady State	T _C = 25°C	I _D	55	A
		T _C = 100°C		39	
Power Dissipation R _{θJC} (Notes 1, 2)		T _C = 25°C	P _D	94	W
		T _C = 100°C		47	
Continuous Drain Current R _{θJA} (Notes 1, 2, 3)	Steady State	T _A = 25°C	I _D	11	A
		T _A = 100°C		8.0	
Power Dissipation R _{θJA} (Notes 1 & 2)		T _A = 25°C	P _D	3.8	W
		T _A = 100°C		1.9	
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs		I _{DM}	140	A
Operating Junction and Storage Temperature			T _J , T _{stg}	-55 to + 175	°C
Source Current (Body Diode)			I _S	60	A
Single Pulse Drain-to-Source Avalanche Energy (T _J = 25°C, V _{DD} = 50 V, V _{GS} = 10 V, I _{L(pk)} = 24 A, L = 0.1 mH, R _G = 25 Ω)			E _{AS}	29	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	1.6	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	40	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



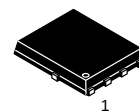
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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
100 V	15 mΩ @ 10 V	55 A

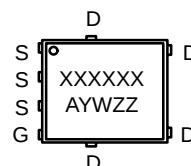


N-CHANNEL MOSFET



DFN5
(SO-8FL)
CASE 488AA
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NVMFS6B14N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			80		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 16\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.0		4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-8.5		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		12.2	15	m Ω

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 50\text{ V}$		1300		pF
Output Capacitance	C_{OSS}			260		
Reverse Transfer Capacitance	C_{RSS}			18		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}, I_D = 20\text{ A}$		20		nC
Threshold Gate Charge	$Q_{G(TH)}$			2.2		
Gate-to-Source Charge	Q_{GS}			6.4		
Gate-to-Drain Charge	Q_{GD}			6.5		
Plateau Voltage	V_{GP}			5.4		V
Gate Resistance	R_G	$T_J = 25^\circ\text{C}$		1.0		Ω

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}, I_D = 20\text{ A}, R_G = 1.0\text{ }\Omega$		9.6		ns
Rise Time	t_r			39		
Turn-Off Delay Time	$t_{d(OFF)}$			16.6		
Fall Time	t_f			6.8		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 20\text{ A}$	$T_J = 25^\circ\text{C}$		0.83	1.2	V
			$T_J = 125^\circ\text{C}$		0.8		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 20\text{ A}$			45		ns
Charge Time	t_a				23		
Discharge Time	t_b				22		
Reverse Recovery Charge	Q_{RR}				50		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

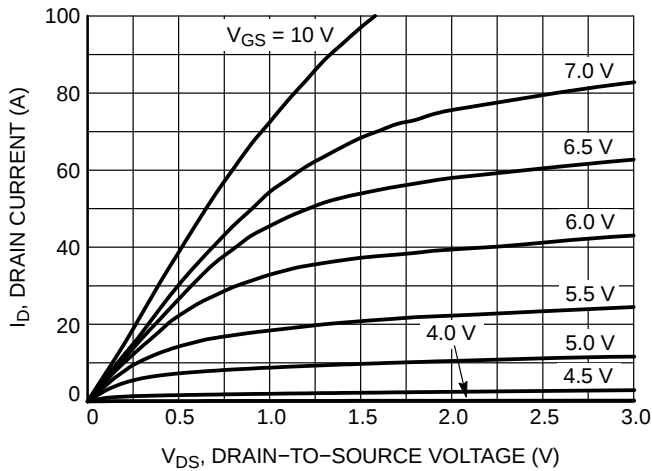


Figure 1. On-Region Characteristics

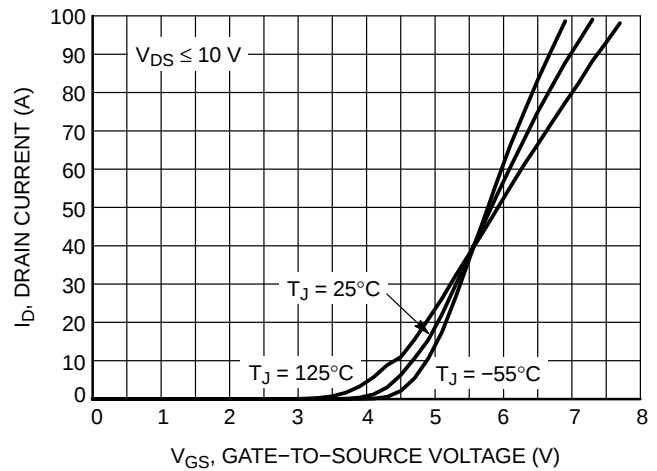


Figure 2. Transfer Characteristics

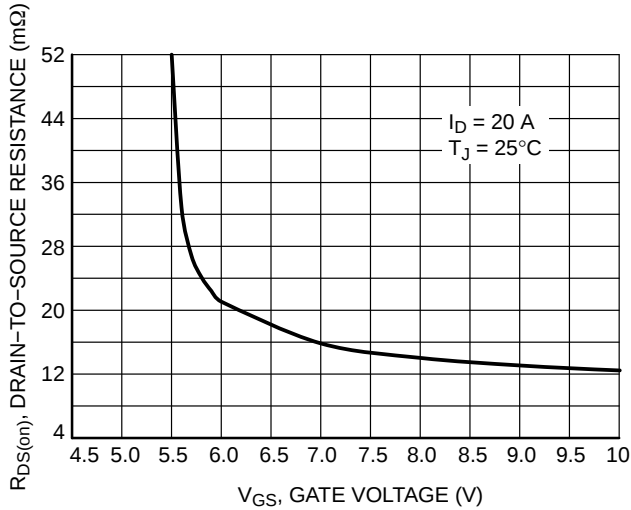


Figure 3. On-Resistance vs. Gate-to-Source Voltage

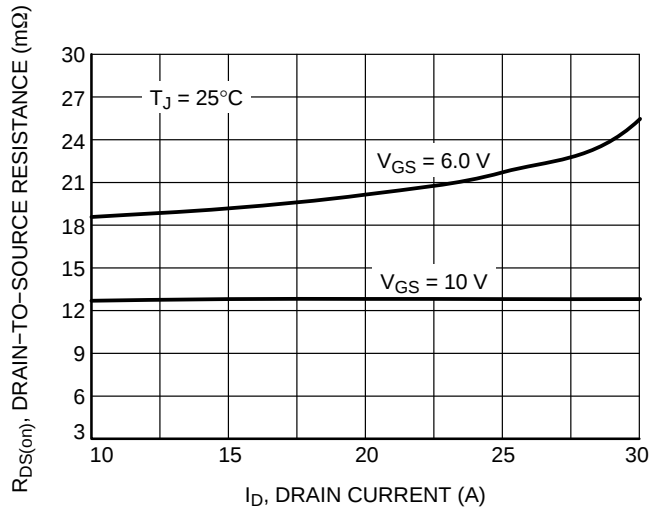


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

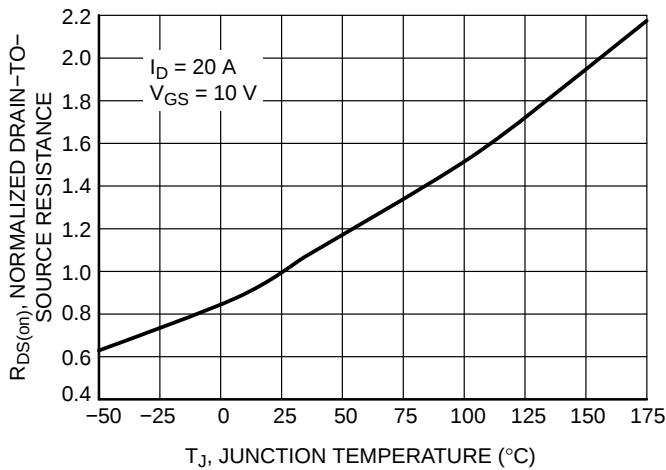


Figure 5. On-Resistance Variation with Temperature

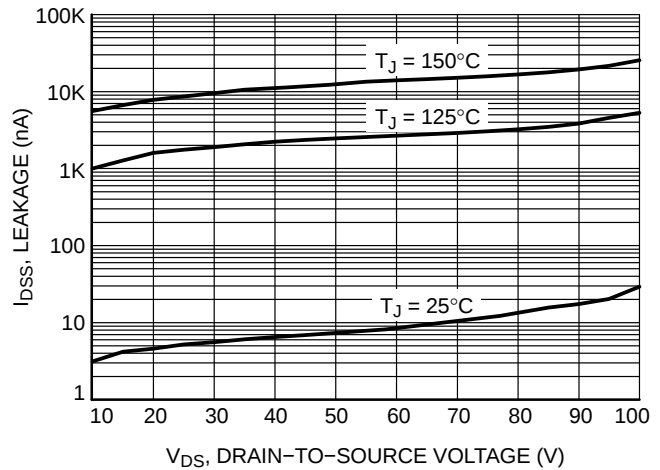


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

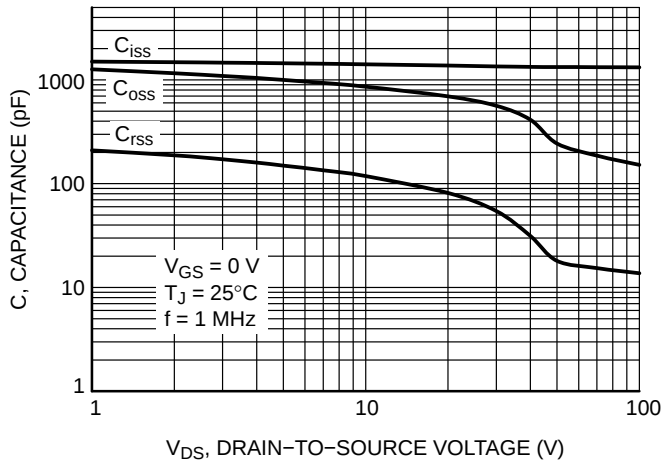


Figure 7. Capacitance Variation

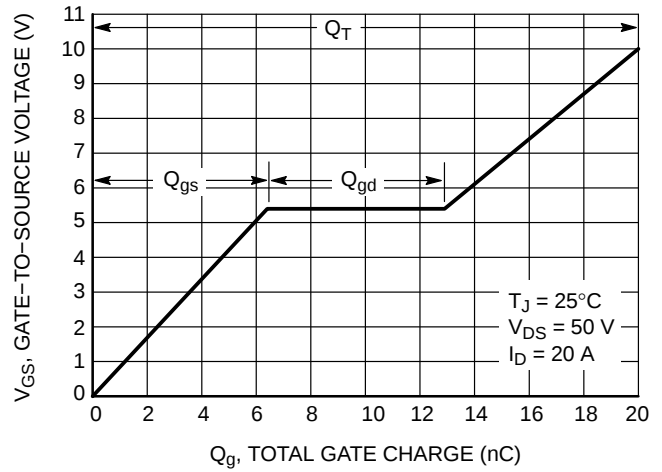


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

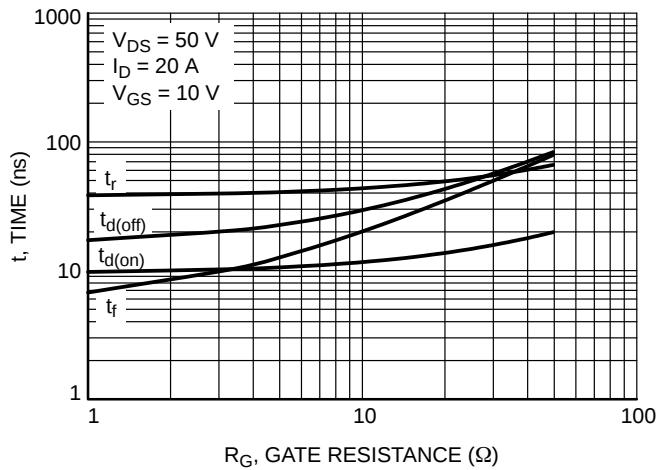


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

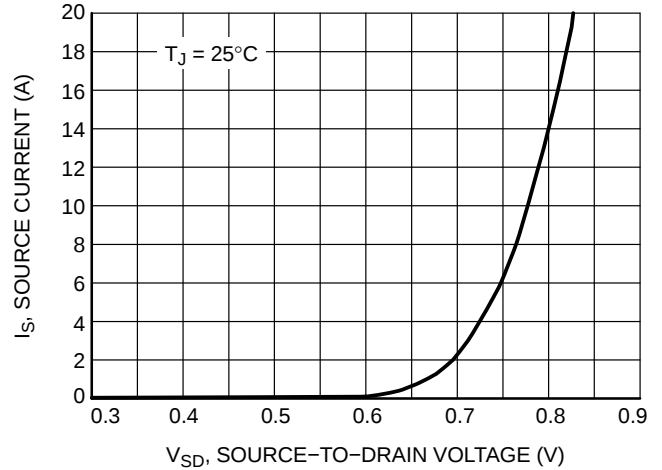


Figure 10. Diode Forward Voltage vs. Current

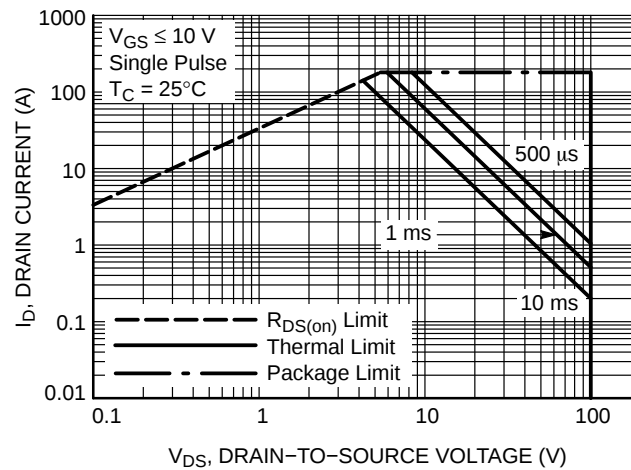


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NVMFS6B14N

TYPICAL CHARACTERISTICS

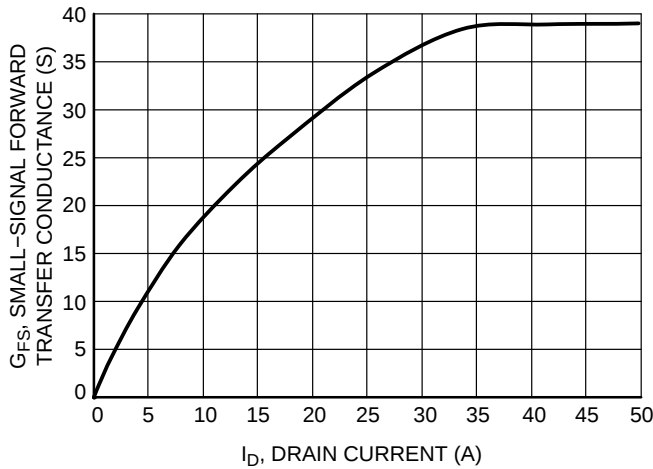


Figure 12. G_{FS} vs. I_D

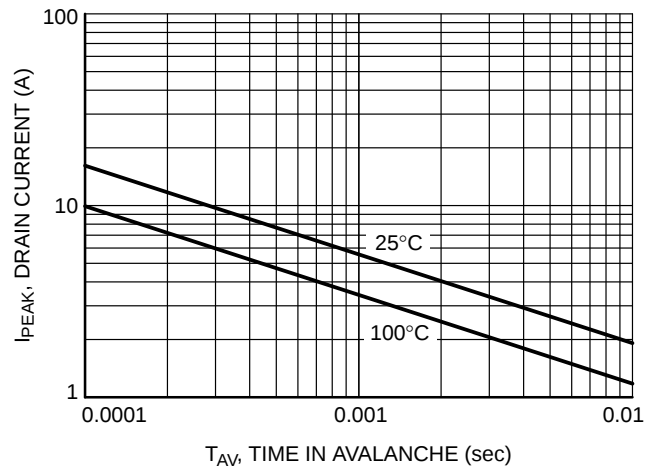


Figure 13. I_{PEAK} vs. T_{AV}

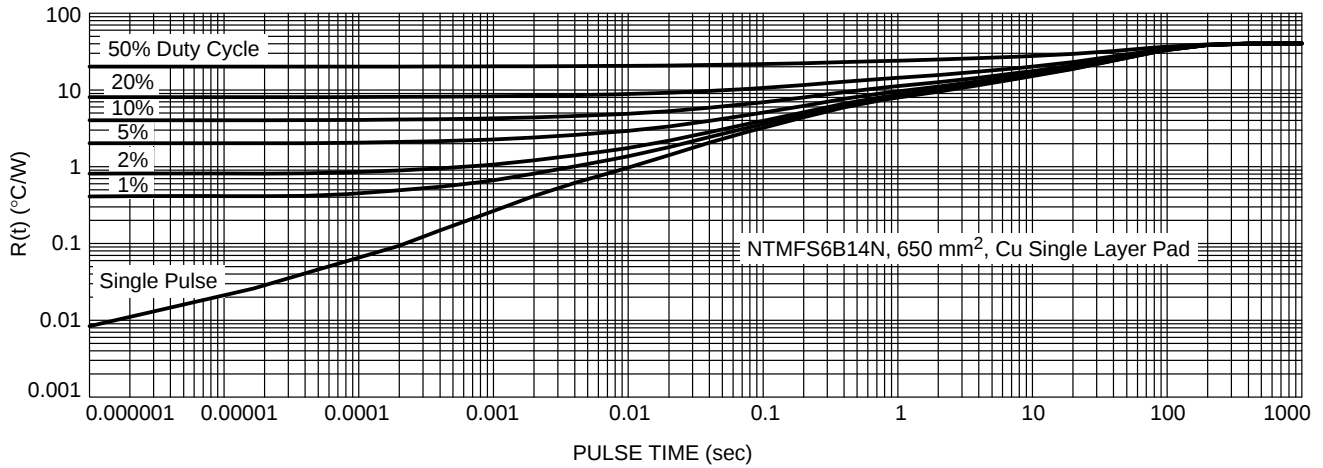


Figure 14. Thermal Response

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFS6B14NT1G	6B14N	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS6B14NWFT1G	6B14WF	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel
NVMFS6B14NT3G	6B14N	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS6B14NWFT3G	6B14WF	DFN5 (Pb-Free, Wettable Flanks)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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- Защита от снятия компонента с производства.



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